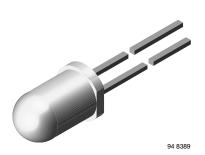
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<u>(5-2008)</u>**



Vishay Semiconductors

High Speed Infrared Emitting Diode, 830 nm, GaAlAs Double Hetero



DESCRIPTION

TSHG8400 is an infrared, 830 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

• Peak wavelength: $\lambda_D = 830 \text{ nm}$

· High reliability

· High radiant power

High radiant intensity

• Angle of half intensity: $\phi = \pm 22^{\circ}$

· Low forward voltage

· Suitable for high pulse current operation

• High modulation bandwidth: f_c = 18 MHz

· Good spectral matching with CMOS cameras

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Note

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- · High speed IR data transmission

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _p (nm)	tr (ns)	
TSHG8400	70	± 22	830	20	

Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM			
TSHG8400	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾			

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V_{R}	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1	A	
Power dissipation		P _V	180	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	t ≤ 5 s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W	





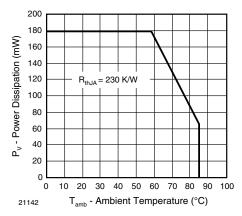


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

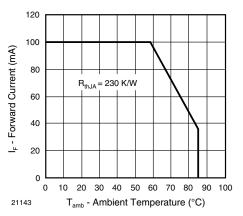


Fig. 1 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Famous de calles de	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.5	1.8	V
Forward voltage	I _F = 1 A, t _p = 100 μs	V _F		2.3		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		125		pF
De die at interestit	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	45	70	135	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$	l _e		700	700	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	φ _e		50		mW
Temperature coefficient of φ _e	I _F = 100 mA	TKφ _e		- 0.35		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I _F = 100 mA	λ_{p}		830		nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ _p	I _F = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	I _F = 100 mA	t _r		20		ns
Fall time	I _F = 100 mA	t _f		13		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c		18		MHz
Virtual source diameter		d		3.7		mm

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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

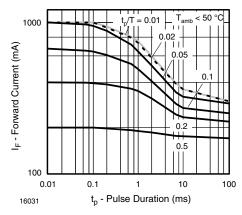


Fig. 2 - Pulse Forward Current vs. Pulse Duration

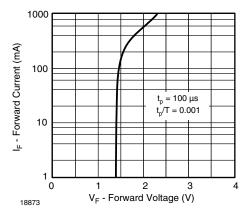


Fig. 3 - Forward Current vs. Forward Voltage

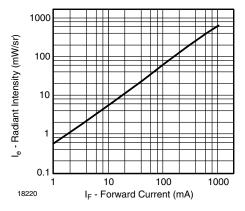


Fig. 4 - Radiant Intensity vs. Forward Current

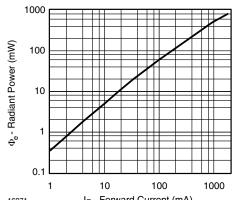


Fig. 5 - Radiant Power vs. Forward Current

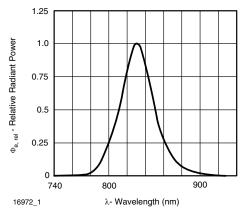


Fig. 6 - Relative Radiant Power vs. Wavelength

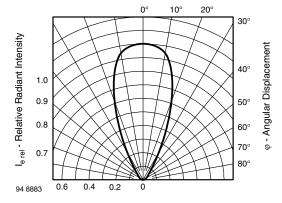
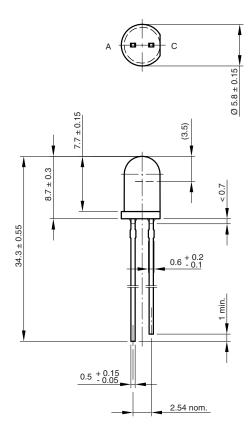
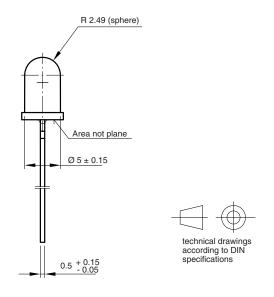


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

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PACKAGE DIMENSIONS in millimeters





Drawing-No.: 6.544-5259.06-4 Issue: 6; 19.05.09 19257



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